

## ESI - HP1000 - HIGH PRESSURE SENSOR

HP1101C3000DE

0-5V (4 wire), 0..3000 bar, 9/16-18UNF-2B, 1M cable  
IP67



- Silicon-on-sapphire sensor technology
- High pressure integrity for safe use due to unique sensor design
- Pressure ranges up to 5,000 bar
- Pressure diaphragm and process connection is machined from one piece of Titanium with no seals or welds.



### PRODUCT DESCRIPTION

The ESI Technology HP1000 high pressure sensors extends the ESI pressure range up to 4000 bar whilst still maintaining an high performance level.

For pressures over 1000 bar the wetted parts and diaphragm are machined from a single piece of titanium alloy which gives this sensor its high pressure integrity and overload capacity. The HP1000 starts from 0 - 600 bar up to the impressive 4000 bar with a total of six standard pressure ranges, four options of outputs including 4-20mA and 0-10V and also four different electrical connections including a DIN connector and M12.

#### Application examples

- Aerospace
- Laboratory and test
- Oil and gas monitoring systems
- Presses
- Test benches

# TECHNICAL DATA

|                          |                                 |
|--------------------------|---------------------------------|
| Ambient temperature      | -40..85°C                       |
| Approvals                | CE, DNV, IEC                    |
| Electrical connection    | 1M Cable outlet screened (IP67) |
| EMC                      | EN61000-6-4, EN61000-6-2        |
| Linearity                | ≤±0.25% BSFL                    |
| Material of wetted parts | Titanium alloy                  |
| Media temperature        | -50..125°C                      |
| Output                   | 0-5V                            |
| Overpressure protection  | 4,500 bar                       |
| Pressure range max       | 3000 bar                        |
| Pressure range min       | 0 bar                           |
| Pressure reference       | Gauge                           |
| Process connection       | Autoclave F-250-C female        |
| Sensor technology        | Silicon-on-Sapphire             |
| Storage temperature      | 5..40°C                         |
| Supply voltage           | 13-30 V DC                      |

